

VRW-56

SQS

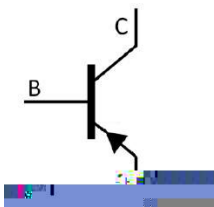
Silicon PNP transistor in a SOT-23 Plastic Package.

H_f

Low frequency.

H_f

Low frequency power amplifier.



PIN 1 Base

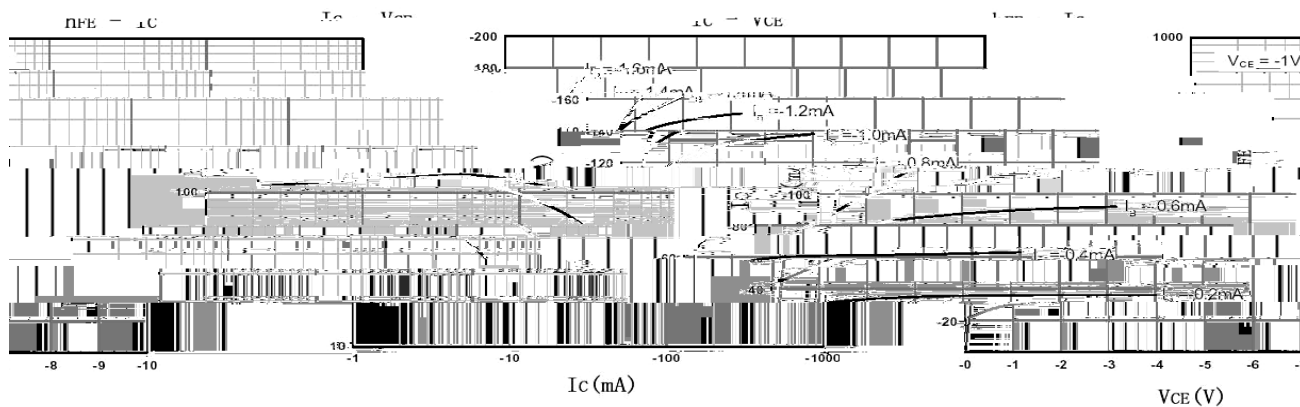
PIN 2 Emitter

PIN 3 Collector

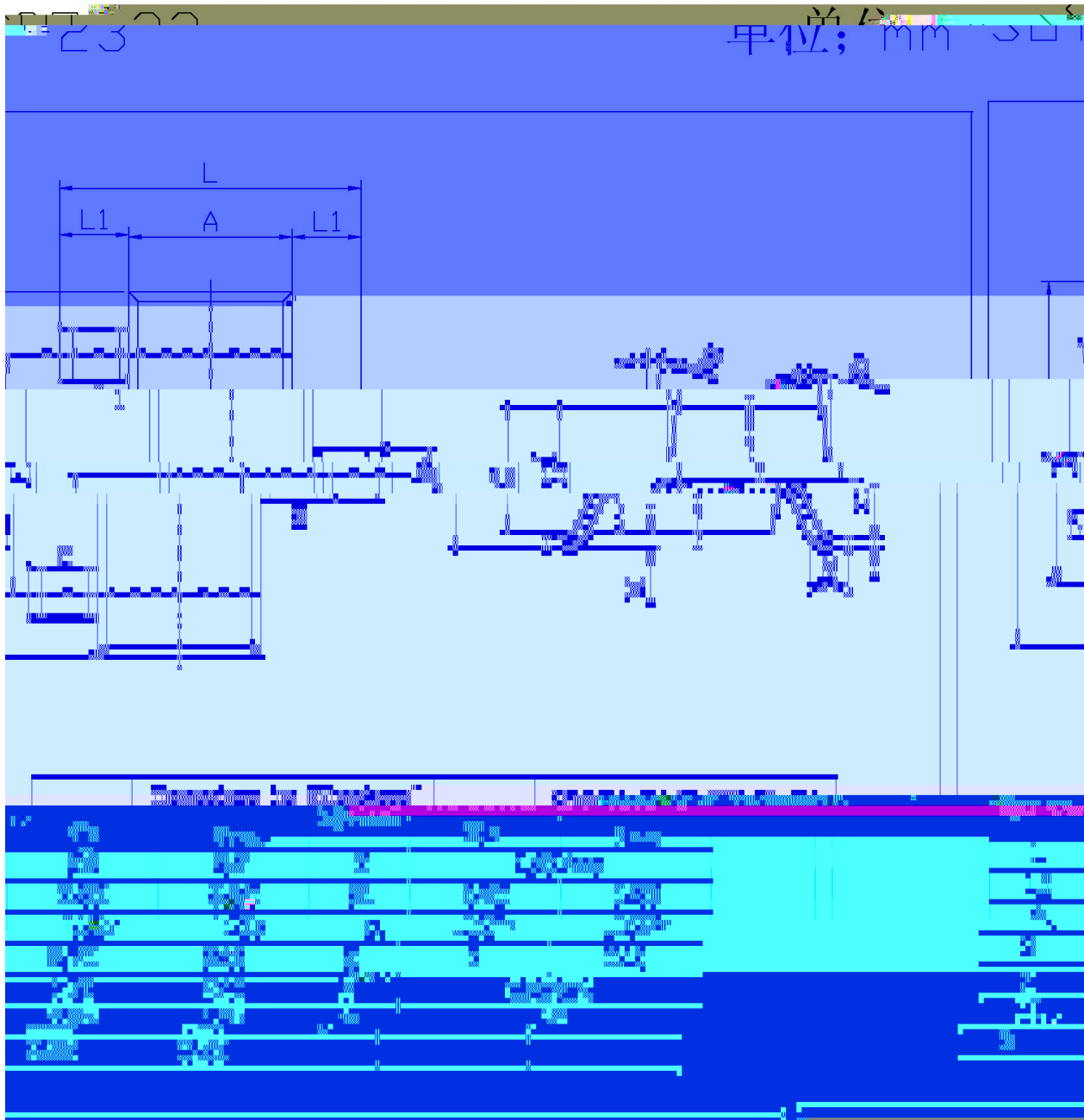
Parameter	N Symbol	Rating	H Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	N Symbol	Test Conditions	Min	Typ	Max	H Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-35V$ $I_E=0$			-0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=-6.0V$ $I_C=-400mA$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-10mA$		-0.1	-0.25	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-100mA$ $V_{CE}=-1.0V$		-0.8	-1.0	V
Transition Frequency	f_T	$I_C=-20mA$ $V_{CE}=-6.0V$		200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6.0V$ $I_E=0$ $f=1.0MHz$				

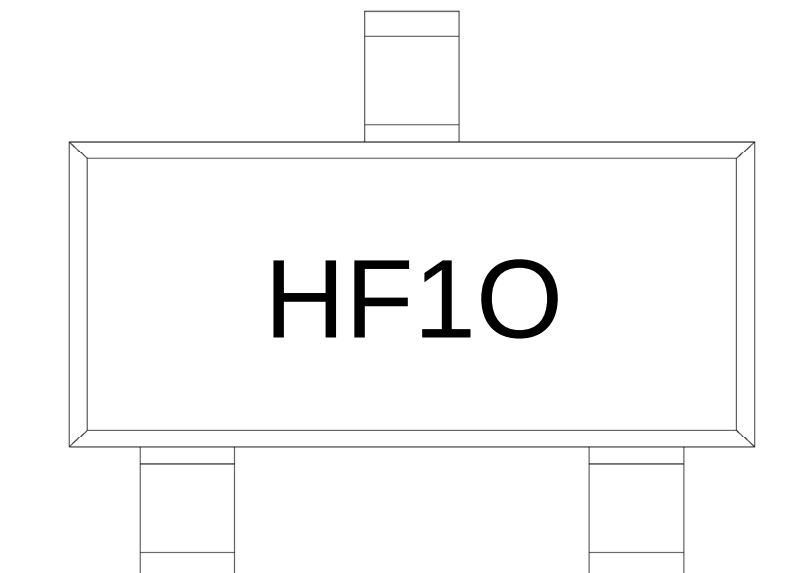
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



H N

I4 N

R h_{IH}

Note:

H Company Code

F1 Product Type Code

O h_{FE} Classifications Symbol Code

() / **Temperature Profile for IR Reflow Soldering(Pb Z**